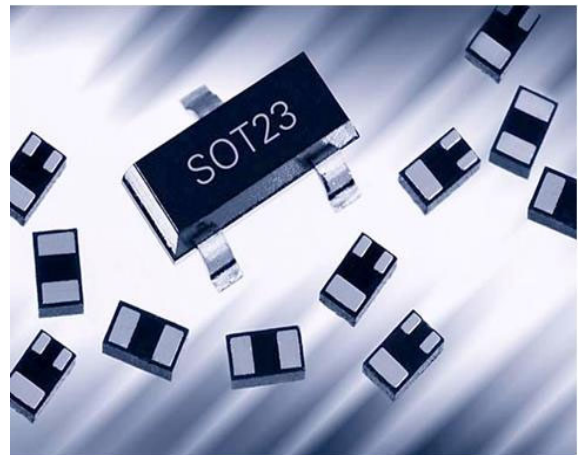


Low Capacitance TVS Diode

- ESD / transient protection of high-speed data lines in 3.3 / 5 / 12 V applications according to:
 - IEC61000-4-2 (ESD): up to ± 25 KV (contact)
 - IEC61000-4-4 (EFT): 40 A (5/50 ns)
 - IEC61000-4-5 (surge): up to 2.5 A (8/20 μ s)
- Smallest form factor down to 1.0 x 0.6 x 0.4 mm
- Max. working voltage: -8 / +14 V or +8 / -14 V
- Ultra low dynamic resistance down to **0.3 Ω**
- Very low capacitance down to 2 pF
- Very low reverse current < 1 nA typ.
- Very low series inductance down to 0.4 nH
- Pb-free (RoHS compliant) package



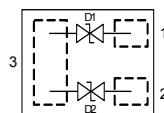
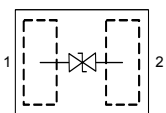
Applications

- USB 2.0, 10/100 Ethernet, Firewire, DVI
- Mobile communication
- Consumer products (STB, MP3, DVD, DSC...)
- LCD displays, camera
- Notebooks and desktop computers, peripherals



ESD8V0L1B-02EL
ESD8V0L1B-02LRH

ESD8V0L2B-03L



Type	Package	Configuration	Marking
ESD8V0L1B-02EL	TSLP-2-18	1 channel, bi-directional	E7
ESD8V0L1B-02LRH	TSLP-2-17	1 channel, bi-directional	B3
ESD8V0L2B-03L	TSLP-3-1	2 channels, bi-directional	B3

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
ESD contact discharge ¹⁾	V_{ESD}		kV
ESD8V0L1B...		25	
ESD8V0L2B..., between all pins		15	
Peak pulse current ($t_p = 8 / 20 \mu\text{s}$) ²⁾	I_{pp}		A
ESD8V0L1B...		2.5	
ESD8V0L2B...		1	
Operating temperature range	T_{op}	-55...125	°C
Storage temperature	T_{stg}	-65...150	

¹⁾ V_{ESD} according to IEC61000-4-2

²⁾ I_{pp} according to IEC61000-4-5

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

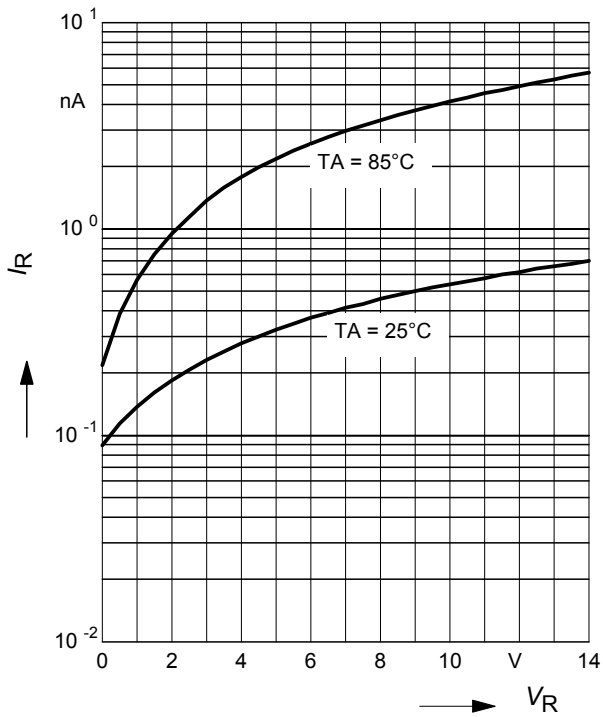
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Reverse working voltage	V_{RWM}	-8	-	14	V
Breakdown voltage	$V_{(BR)}$				
$I_{(BR)} = 1 \text{ mA}$, from pin 2 to 1, ESD8V0L1B...		14.5	-	-	
$I_{(BR)} = 1 \text{ mA}$, from pin 1 to 2, ESD8V0L1B...		8.5	-	-	
$I_{(BR)} = 1 \text{ mA}$, from pin 1/2 to 3, ESD8V0L2B...		14.5	-	-	
$I_{(BR)} = 1 \text{ mA}$, from pin 3 to 1/2, ESD8V0L2B...		8.5	-	-	
$I_{(BR)} = 1 \text{ mA}$, from pin 1 to 2, ESD8V0L2B...		23	-	-	
Reverse current $V_R = 3 \text{ V}$, between all pins	I_R	-	< 1	50	nA
Clamping voltage (contact) ¹⁾	V_{CL}				V
$V_{ESD} = +15 \text{ kV}$, from pin 1 to 2, ESD8V0L1B...		-	21	-	
$V_{ESD} = -15 \text{ kV}$, from pin 1 to 2, ESD8V0L1B...		-	16	-	
$V_{ESD} = +15 \text{ kV}$, from pin 1/2 to 3, ESD8V0L2B...		-	26	-	
$V_{ESD} = -15 \text{ kV}$, from pin 1/2 to 3, ESD8V0L2B...		-	20	-	
Line capacitance ²⁾	C_T				pF
$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, ESD8V0L1B...		-	8.5	13	
$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, ESD8V0L2B..., from pin 1/2 to 3		-	4	7	
from pin 1 to 2, pin 3 is not connected		-	2	4	
Dynamic resistance ($t_p=30\text{ns}$)	R_D				Ω
ESD8V0L1B...		-	0.3	-	
ESD8V0L2B...		-	0.6	-	

¹⁾ V_{ESD} according to IEC61000-4-2

²⁾Total capacitance line to ground

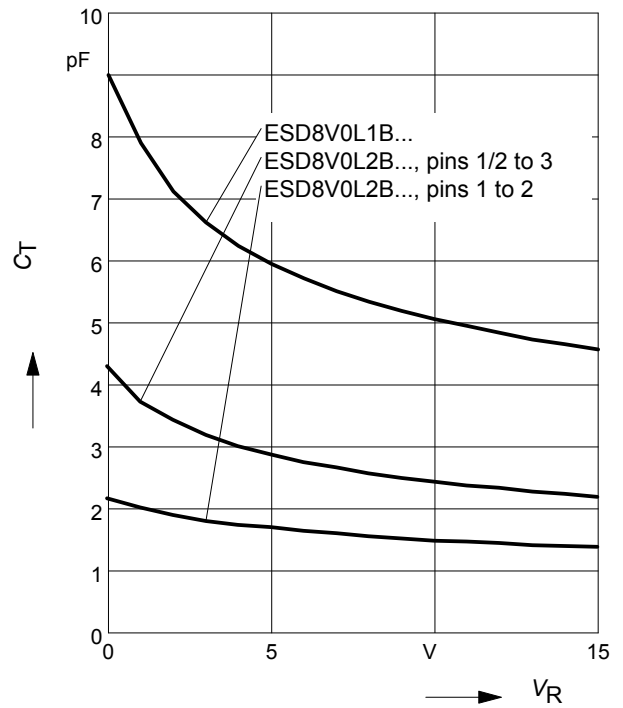
Reverse current $I_R = f(V_R)$

$T_A =$ Parameter



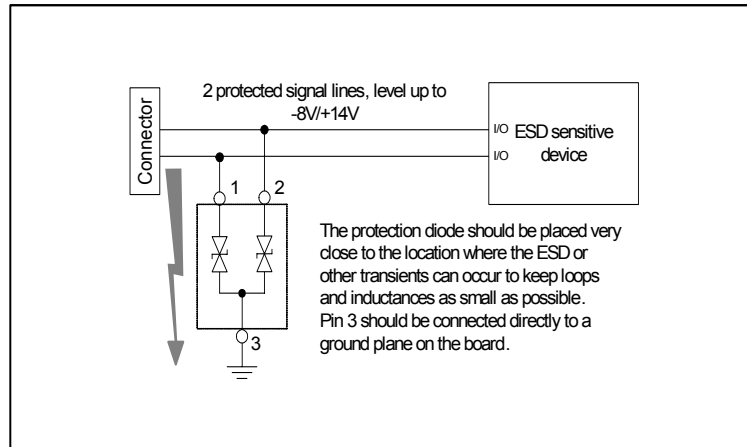
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



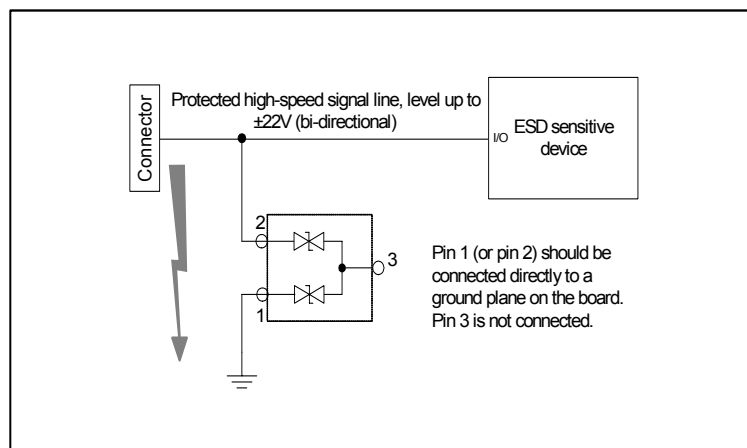
Application example ESD8V0L2B...

2 channels, bi-directional



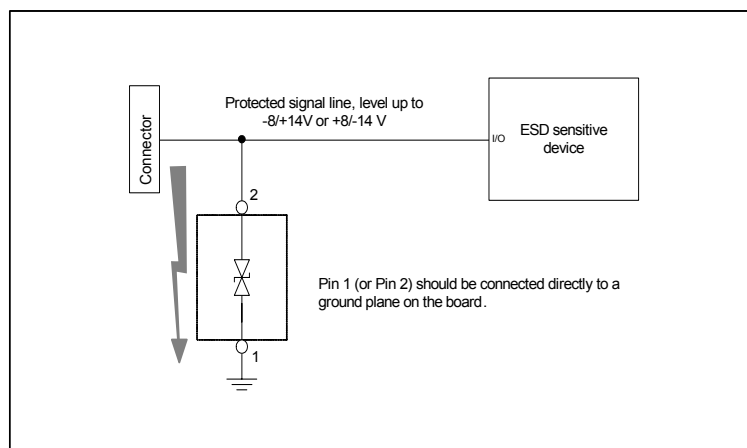
Application example ESD8V0L2B...

1 high-speed channel, bi-directional

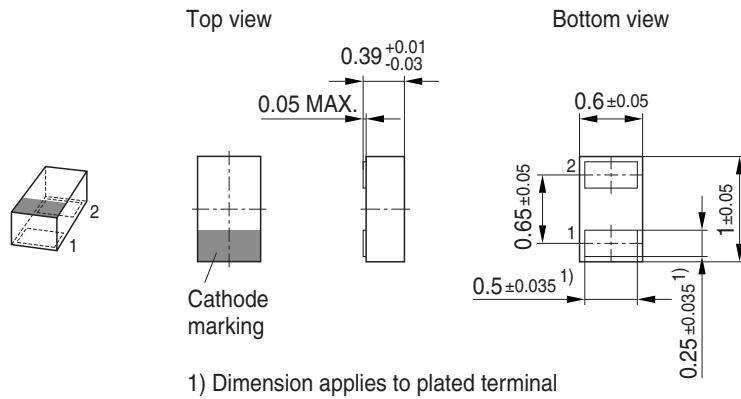


Application example ESD8V0L1B...

1 channel, bi-directional

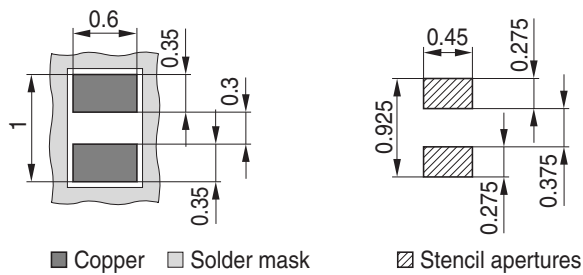


Package Outline

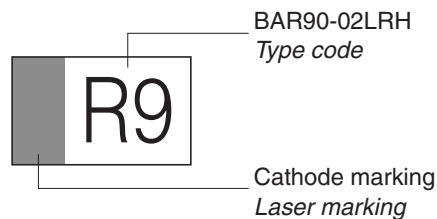


Foot Print

For board assembly information please refer to Infineon website "Packages"

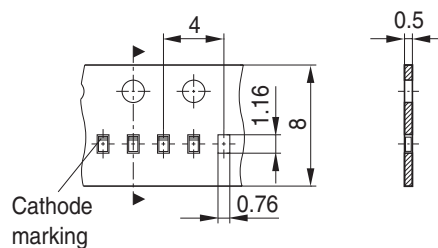


Marking Layout (Example)

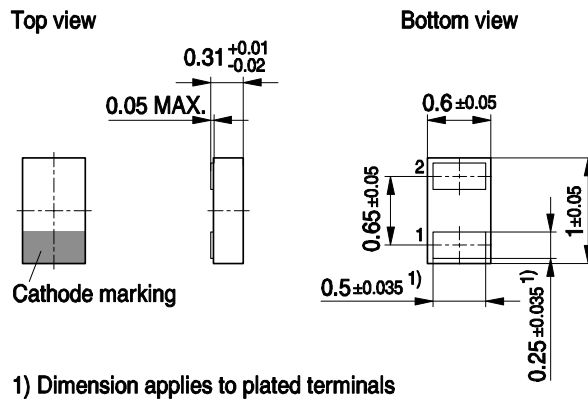


Standard Packing

Reel \varnothing 180 mm = 15.000 Pieces/Reel
 Reel \varnothing 330 mm = 50.000 Pieces/Reel (optional)

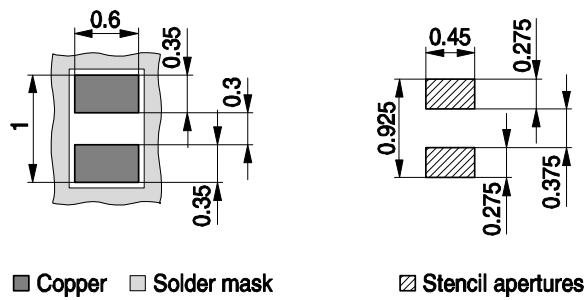


Package Outline

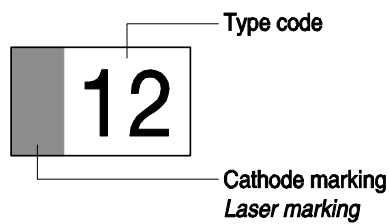


Foot Print

For board assembly information please refer to Infineon website "Packages"

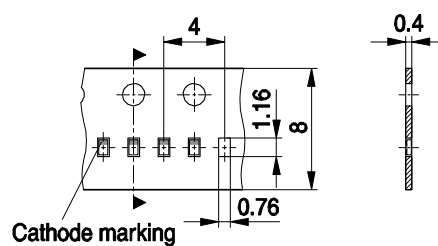


Marking Layout

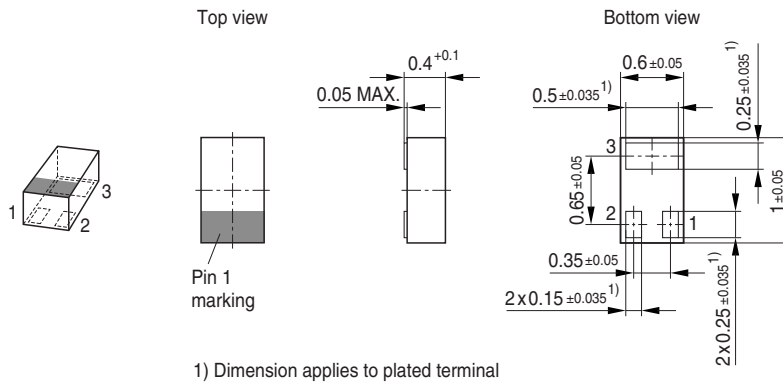


Standard Packing

Reel \varnothing 330 mm = 15.000 Pieces/Reel

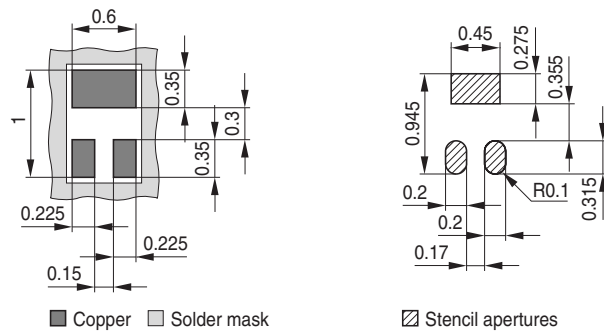


Package Outline

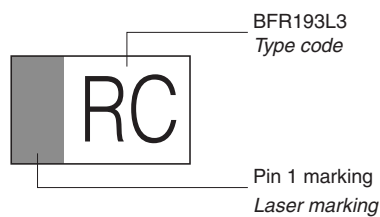


Foot Print

For board assembly information please refer to Infineon website "Packages"

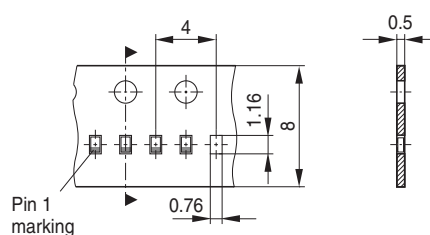


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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